



1214-110V

110 Watts - 50 Volts, 330 μ s, 10%
Radar 1200 - 1400 MHz

GENERAL DESCRIPTION

The 1214-110V is an internally matched, COMMON BASE transistor capable of providing 110 Watts of pulsed RF output power at 330 μ s pulse width, 10% duty factor across the band 1200 to 1400 MHz. This hermetically solder-sealed transistor is specifically designed for L-Band radar applications. It utilizes gold metallization and diffused emitter ballasting to provide high reliability and supreme ruggedness.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C 270 Watts

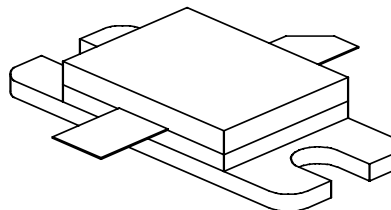
Maximum Voltage and Current

BVces	Collector to Emitter Voltage	75 Volts
BVebo	Emitter to Base Voltage	3.0 Volts
Ic	Collector Current	8 Amps

Maximum Temperatures

Storage Temperature	- 65 to + 200°C
Operating Junction Temperature	+ 200°C

CASE OUTLINE 55KT, STYLE 1



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout	Power Out	Freq = 1200 – 1400 MHz	110		160	Watts
Pg	Power Gain	Vcc = 50 Volts	7.4			dB
η_c	Collector Efficiency	Pin = 20 Watts	50	55		%
RI	Input Return loss	Pulse Width = 330 μ s	10			dB
Droop	Droop	Duty Factor = 10%			0.5	dB
Flatness	Flatness				1.0	dB
VSWR-S	Load Mismatch Stability				1.5:1	
VSWR-T	Load Mismatch Tolerance				3.0:1	

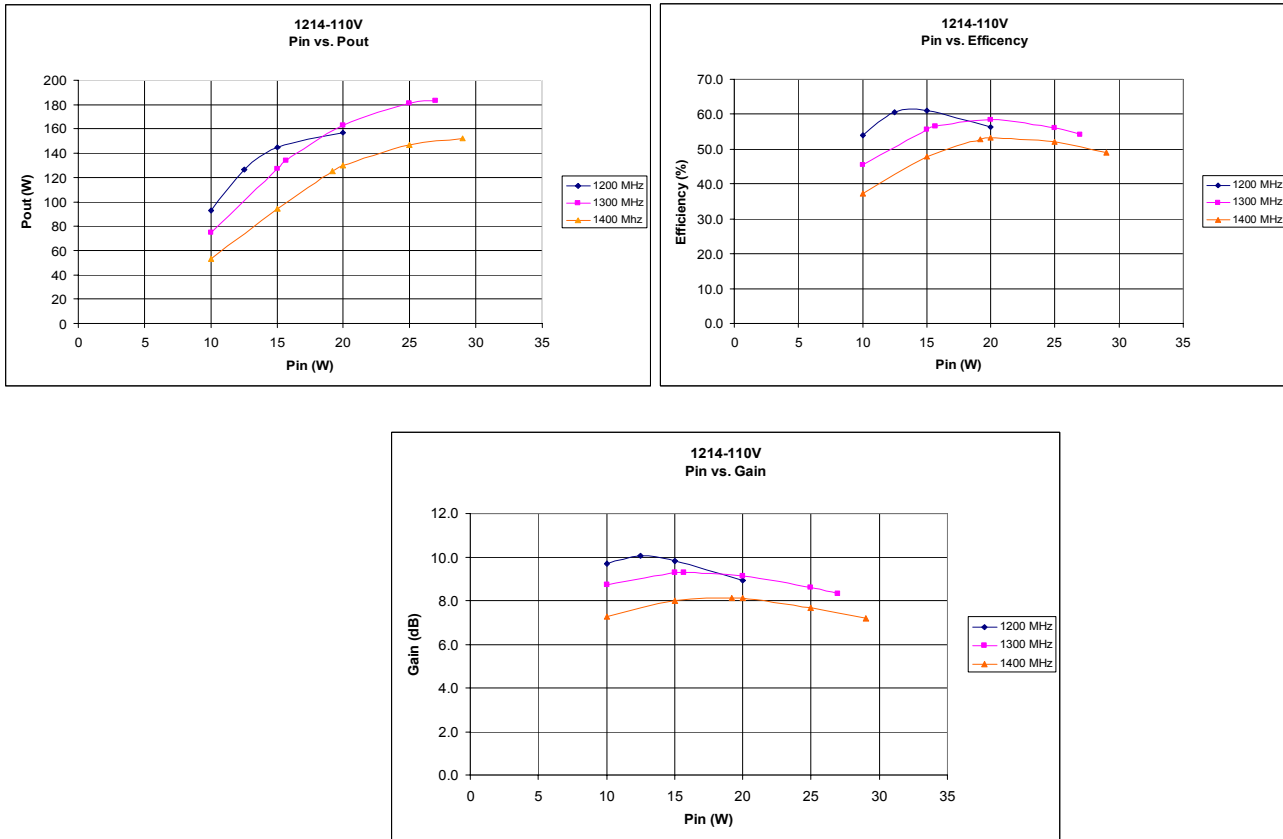
FUNCTIONAL CHARACTERISTICS @ 25°C

Bvces	Collector to Emitter Breakdown	Ic = 100 mA	75			Volts
Ices	Collector to Emitter Leakage	Vce = 50 Volts			10	mA
θ_{jc}^1	Thermal Resistance	Rated Pulse Condition			0.5	°C/W

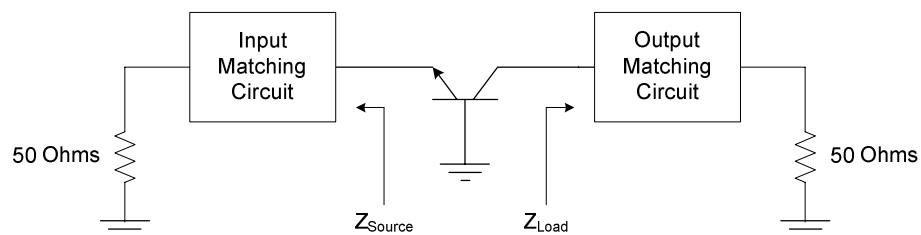


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Performance Curves



Impedance Information



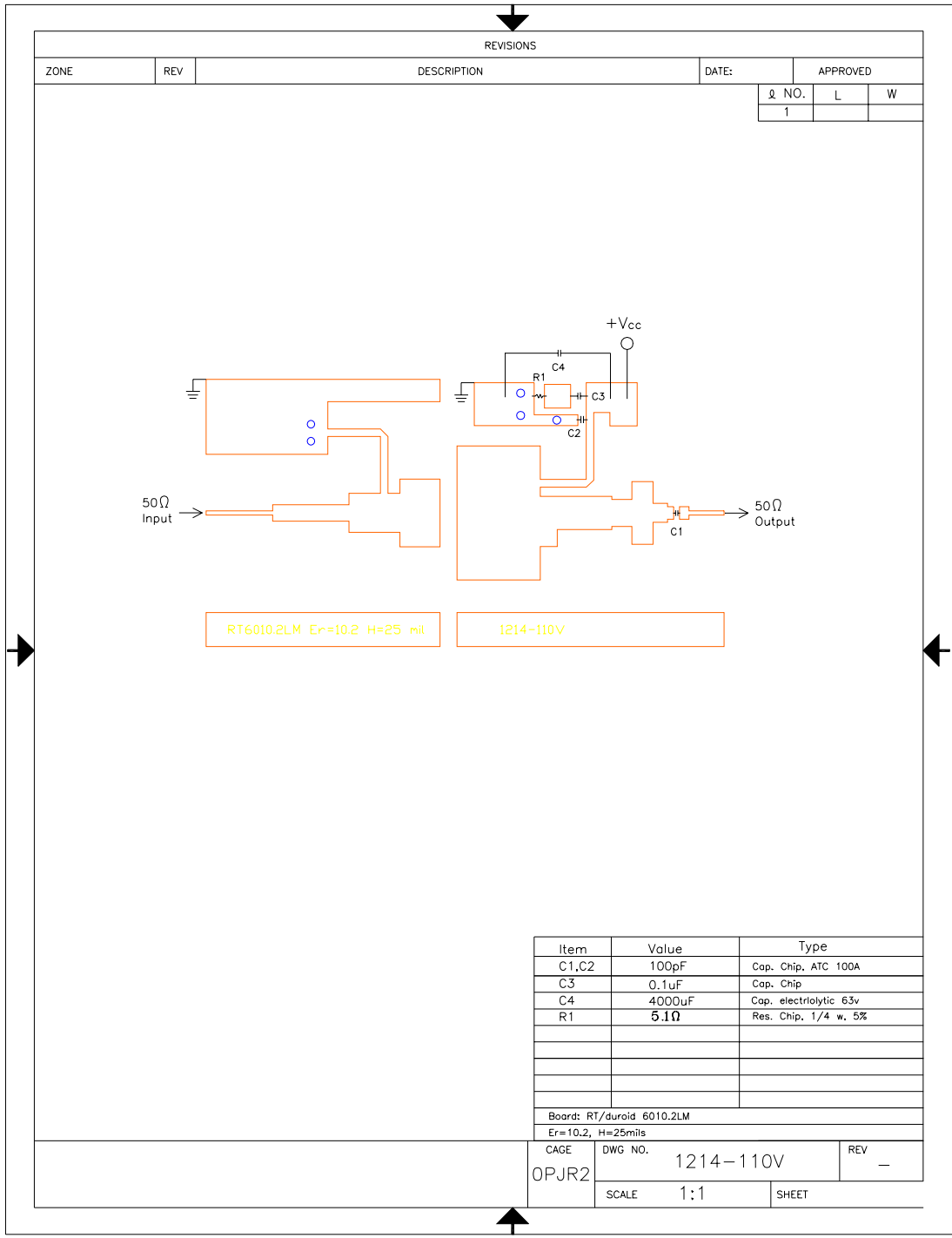
Frequencies (MHz)	$Z_{Source} (\Omega)$	$Z_{Load} (\Omega)^2$
1200	3.36-j3.12	4.97+j0.15
1300	3.5-j2.4	5.33-j2.86
1400	3.81-j1.3	2.88-j3.86

Note 2: Z_{Load} exclusive of bias circuit



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Test Circuit





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